

General Description

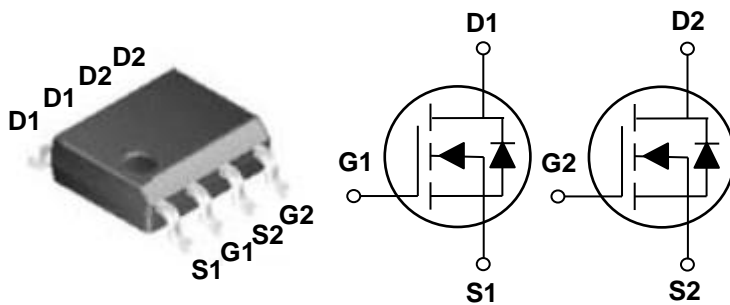
These N-Channel enhancement mode power field effect transistors are using trench DMOS technology. This advanced technology has been especially tailored to minimize on-state resistance, provide superior switching performance, and withstand high energy pulse in the avalanche and commutation mode. These devices are well suited for high efficiency fast switching applications.

| | | |
|-------|-------|----|
| BVDSS | RDSON | ID |
| 30V | 11mΩ | 9A |

Features

- 30V,9A, $R_{DS(ON)} = 11m\Omega @ V_{GS} = 10V$
- Improved dv/dt capability
- Fast switching
- Green Device Available

Dual SOP8 Pin Configuration



Applications

- MB / VGA / Vcore
- POL Applications
- SMPS 2nd SR



Absolute Maximum Ratings $T_c=25^\circ\text{C}$ unless otherwise noted

| Symbol | Parameter | Rating | Units |
|-----------|---|------------|---------------------|
| V_{DS} | Drain-Source Voltage | 30 | V |
| V_{GS} | Gate-Source Voltage | ± 20 | V |
| I_D | Drain Current – Continuous ($T_A=25^\circ\text{C}$) | 9 | A |
| | Drain Current – Continuous ($T_A=70^\circ\text{C}$) | 7.2 | A |
| I_{DM} | Drain Current – Pulsed ¹ | 36 | A |
| P_D | Power Dissipation ($T_A=25^\circ\text{C}$) | 1.47 | W |
| | Power Dissipation – Derate above 25°C | 0.01 | W/ $^\circ\text{C}$ |
| T_{STG} | Storage Temperature Range | -55 to 150 | $^\circ\text{C}$ |
| T_J | Operating Junction Temperature Range | -55 to 150 | $^\circ\text{C}$ |

Thermal Characteristics

| Symbol | Parameter | Typ. | Max. | Unit |
|-----------------|--|------|------|--------------------|
| $R_{\theta JA}$ | Thermal Resistance Junction to ambient | --- | 85 | $^\circ\text{C/W}$ |

Electrical Characteristics (T_J=25 °C, unless otherwise noted)
Off Characteristics

| Symbol | Parameter | Conditions | Min. | Typ. | Max. | Unit |
|-------------------------------------|---|--|------|------|------|------|
| BV _{DSS} | Drain-Source Breakdown Voltage | V _{GS} =0V, I _D =250uA | 30 | --- | --- | V |
| ΔBV _{DSS} /ΔT _J | BV _{DSS} Temperature Coefficient | Reference to 25°C, I _D =1mA | --- | 0.04 | --- | V/°C |
| I _{DSS} | Drain-Source Leakage Current | V _{DS} =30V, V _{GS} =0V, T _J =25°C | --- | --- | 1 | uA |
| | | V _{DS} =24V, V _{GS} =0V, T _J =125°C | --- | --- | 10 | uA |
| I _{GSS} | Gate-Source Leakage Current | V _{GS} =±20V, V _{DS} =0V | --- | --- | ±100 | nA |

On Characteristics

| | | | | | | |
|----------------------|--|--|-----|------|-----|-------|
| R _{DS(ON)} | Static Drain-Source On-Resistance ³ | V _{GS} =10V, I _D =6A | --- | 8.6 | 11 | mΩ |
| | | V _{GS} =4.5V, I _D =3A | --- | 10.8 | 15 | mΩ |
| V _{GS(th)} | Gate Threshold Voltage | V _{GS} =V _{DS} , I _D =250uA | 1.2 | 1.6 | 2.5 | V |
| ΔV _{GS(th)} | V _{GS(th)} Temperature Coefficient | | --- | -4 | --- | mV/°C |
| g _{fs} | Forward Transconductance | V _{DS} =10V, I _D =8A | --- | 10 | --- | S |

Dynamic and switching Characteristics

| | | | | | | |
|---------------------|-------------------------------------|---|-----|------|------|----|
| Q _g | Total Gate Charge ^{2, 3} | V _{DS} =15V, V _{GS} =10V, I _D =6A | --- | 16.6 | 33 | nC |
| Q _{gs} | Gate-Source Charge ^{2, 3} | | --- | 1.3 | 3 | |
| Q _{gd} | Gate-Drain Charge ^{2, 3} | | --- | 4.5 | 9 | |
| T _{d(on)} | Turn-On Delay Time ^{2, 3} | V _{DD} =15V, V _{GS} =10V, R _G =3.3Ω I _D =15A | --- | 4.8 | 9 | ns |
| T _r | Rise Time ^{2, 3} | | --- | 12.5 | 25 | |
| T _{d(off)} | Turn-Off Delay Time ^{2, 3} | | --- | 27.6 | 50 | |
| T _f | Fall Time ^{2, 3} | | --- | 8.2 | 16 | |
| C _{iss} | Input Capacitance | V _{DS} =25V, V _{GS} =0V, F=1MHz | --- | 750 | 1350 | pF |
| C _{oss} | Output Capacitance | | --- | 150 | 300 | |
| C _{rss} | Reverse Transfer Capacitance | | --- | 110 | 200 | |
| R _g | Gate resistance | V _{GS} =0V, V _{DS} =0V, F=1MHz | --- | 2.7 | 4.5 | Ω |

Drain-Source Diode Characteristics and Maximum Ratings

| Symbol | Parameter | Conditions | Min. | Typ. | Max. | Unit |
|-----------------|------------------------------------|---|------|------|------|------|
| I _S | Continuous Source Current | V _G =V _D =0V, Force Current | --- | --- | 9 | A |
| I _{SM} | Pulsed Source Current ³ | | --- | --- | 18 | A |
| V _{SD} | Diode Forward Voltage ³ | V _{GS} =0V, I _S =1A, T _J =25°C | --- | --- | 1 | V |

Note :

1. Repetitive Rating : Pulsed width limited by maximum junction temperature.
2. The data tested by pulsed, pulse width ≤ 300us, duty cycle ≤ 2%.
3. Essentially independent of operating temperature.

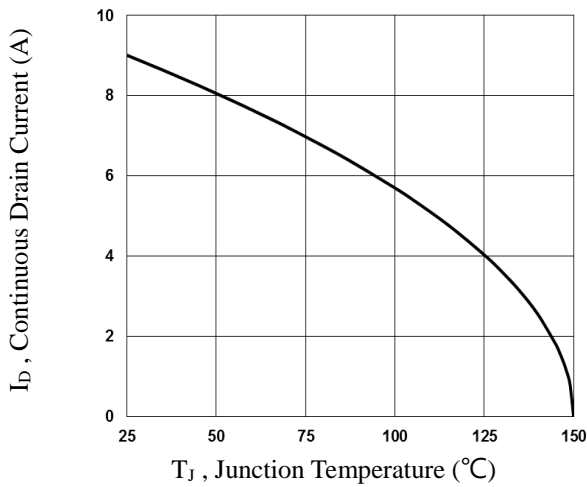


Fig.1 Continuous Drain Current vs. T_c

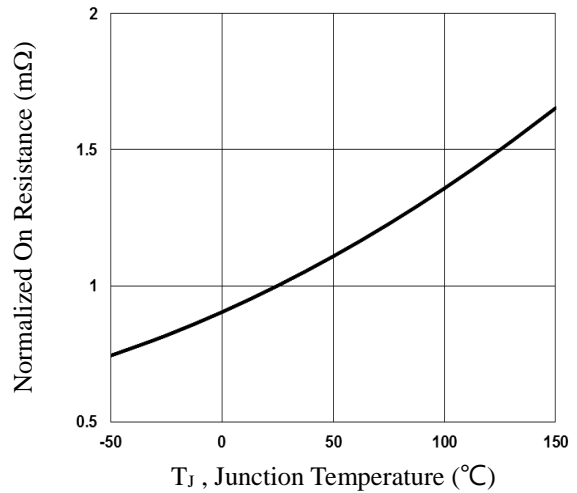


Fig.2 Normalized $R_{DS(on)}$ vs. T_J

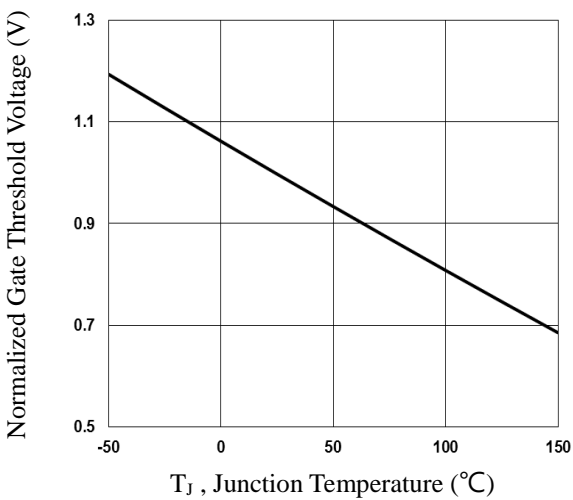


Fig.3 Normalized V_{th} vs. T_J

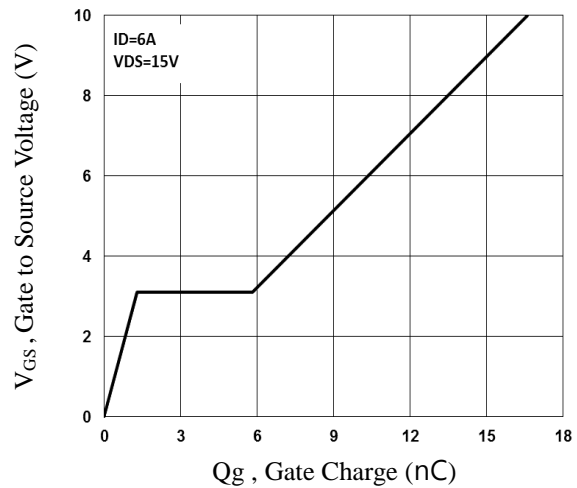


Fig.4 Gate Charge Waveform

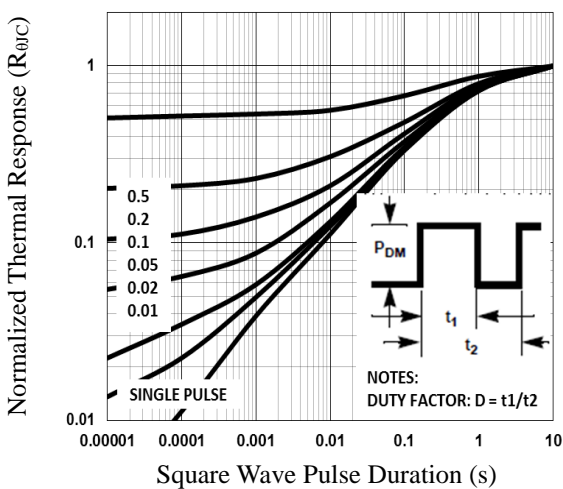


Fig.5 Normalized Transient Impedance

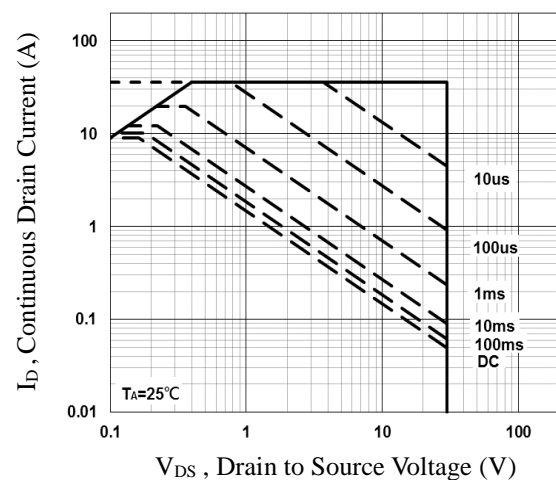


Fig.6 Maximum Safe Operation Area

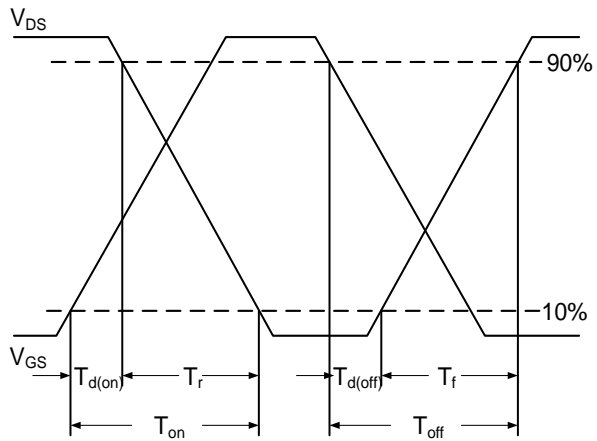


Fig.7 Switching Time Waveform

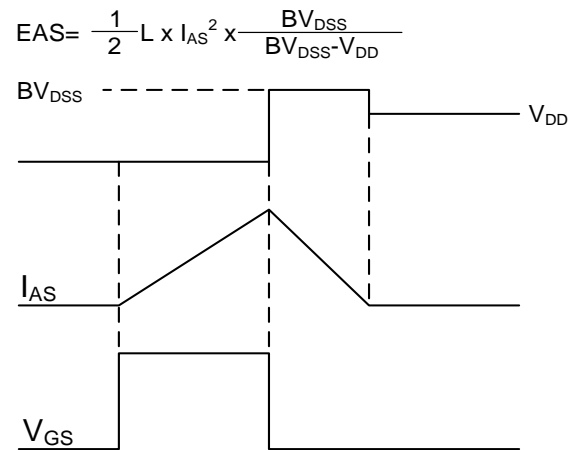
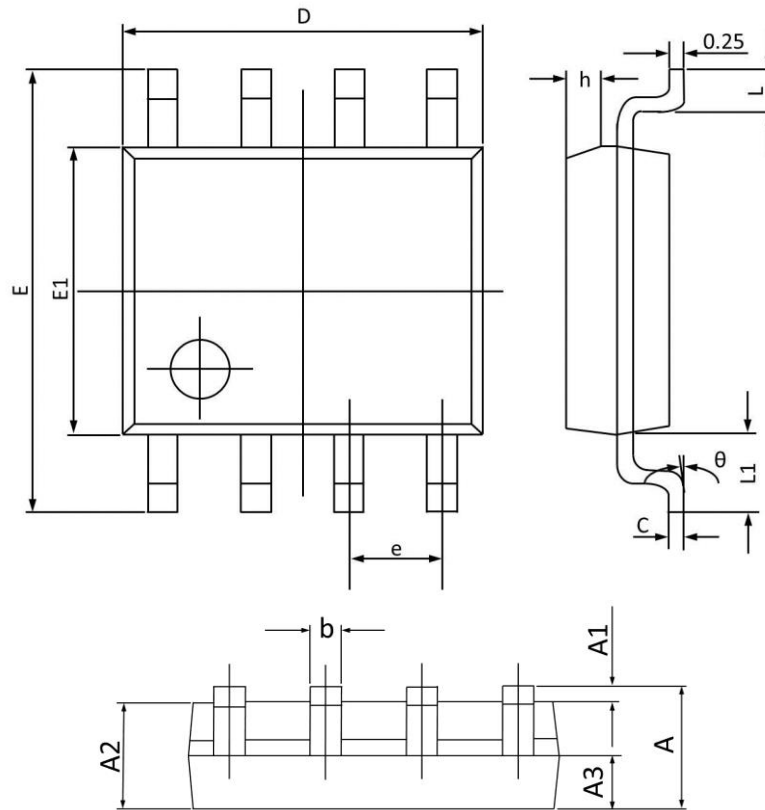


Fig.8 EAS Waveform

$$EAS = \frac{1}{2} L \times I_{AS}^2 \times \frac{BV_{DSS}}{BV_{DSS} - V_{DD}}$$

SOP8 PACKAGE INFORMATION



| Symbol | Dimensions In Millimeters | | Dimensions In Inches | |
|----------|---------------------------|-------|----------------------|-------|
| | Min | Max | Min | Max |
| A | 1.350 | 1.750 | 0.053 | 0.068 |
| A1 | 0.100 | 0.250 | 0.004 | 0.009 |
| A2 | 1.300 | 1.500 | 0.052 | 0.059 |
| A3 | 0.600 | 0.700 | 0.024 | 0.027 |
| b | 0.390 | 0.480 | 0.016 | 0.018 |
| c | 0.210 | 0.260 | 0.009 | 0.010 |
| D | 4.700 | 5.100 | 0.186 | 0.200 |
| E | 5.800 | 6.200 | 0.229 | 0.244 |
| E1 | 3.700 | 4.100 | 0.146 | 0.161 |
| e | 1.270(BSC) | | 0.050(BSC) | |
| h | 0.250 | 0.500 | 0.010 | 0.019 |
| L | 0.500 | 0.800 | 0.019 | 0.031 |
| L1 | 1.050(BSC) | | 0.041(BSC) | |
| θ | 0° | 8° | 0° | 8° |